Mingxiang Wang

List of Publications by Year
in descending order

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58	801	623734	552781
papers	citations	14 h-index	26 g-index

58	58	58	389
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High performance low temperature metal-induced unilaterally crystallized polycrystalline silicon thin film transistors for system-on-panel applications. IEEE Transactions on Electron Devices, 2000, 47, 404-409.	3.0	163
2	Degradation Behaviors of Metal-Induced Laterally Crystallized n-Type Polycrystalline Silicon Thin-Film Transistors Under DC Bias Stresses. IEEE Transactions on Electron Devices, 2007, 54, 225-232.	3.0	46
3	The effects of high temperature annealing on metal-induced laterally crystallized polycrystalline silicon. IEEE Transactions on Electron Devices, 2000, 47, 2061-2067.	3.0	42
4	An Effective Channel Mobility-Based Analytical On-Current Model for Polycrystalline Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2007, 54, 869-874.	3.0	41
5	Analysis of Degradation Mechanisms in Low-Temperature Polycrystalline Silicon Thin-Film Transistors under Dynamic Drain Stress. IEEE Transactions on Electron Devices, 2012, 59, 1730-1737.	3.0	33
6	Stress Power Dependent Self-Heating Degradation of Metal-Induced Laterally Crystallized n-Type Polycrystalline Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2007, 54, 3276-3284.	3.0	29
7	Characterization of an individual grain boundary in metal-induced laterally crystallized polycrystalline silicon thin-film devices. IEEE Transactions on Electron Devices, 2001, 48, 1655-1660.	3.0	28
8	Negative Bias Temperature Instability Dominated Degradation of Metal-Induced Laterally Crystallized p-Type Polycrystalline Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2009, 56, 587-594.	3.0	27
9	Degradation of Metal-Induced Laterally Crystallized n-Type Polycrystalline Silicon Thin-Film Transistors Under Synchronized Voltage Stress. IEEE Transactions on Electron Devices, 2009, 56, 2726-2732.	3.0	23
10	Dynamic degradation of a-InGaZnO thin-film transistors under pulsed gate voltage stress. Applied Physics Letters, 2015, 106, .	3.3	19
11	A Unified Degradation Model of a-InGaZnO TFTs Under Negative Gate Bias With or Without an Illumination. IEEE Journal of the Electron Devices Society, 2019, 7, 1063-1071.	2.1	19
12	Two-Stage Degradation of p-Channel Poly-Si Thin-Film Transistors Under Dynamic Negative Bias Temperature Stress. IEEE Transactions on Electron Devices, 2011, 58, 3034-3041.	3.0	18
13	Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. IEEE Transactions on Electron Devices, 2021, 68, 1649-1653.	3.0	16
14	Anisotropic conduction behavior in metal-induced laterally crystallized polycrystalline silicon thin films. Applied Physics Letters, 2000, 76, 448-450.	3.3	15
15	Spontaneous Degradation of Flexible Poly-Si TFTs Subject to Dynamic Bending Stress. IEEE Transactions on Electron Devices, 2019, 66, 2214-2218.	3.0	15
16	An Analytical Subthreshold Model of Polycrystalline Silicon Thin-Film Transistors Based on Meyer-Neldel Rule. IEEE Transactions on Electron Devices, 2014, 61, 863-869.	3.0	14
17	Suppression of the Short-Channel Effect in Dehydrogenated Elevated-Metal Metal- Oxide (EMMO) Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3001-3004.	3.0	14
18	An investigation of drain pulse induced hot carrier degradation in n-type low temperature polycrystalline silicon thin film transistors. Microelectronics Reliability, 2010, 50, 713-716.	1.7	13

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19	High-Mobility Amorphous InGaZnO Thin-Film Transistors With Nitrogen Introduced via Low-Temperature Annealing. IEEE Electron Device Letters, 2021, 42, 1480-1483.	3.9	13
20	Suppress Dynamic Hot-Carrier Induced Degradation in Polycrystalline Si Thin-Film Transistors by Using a Substrate Terminal. IEEE Electron Device Letters, 2014, 35, 551-553.	3.9	12
21	Mechanical Reliability of Flexible a-InGaZnO TFTs under Dynamic Stretch Stress. IEEE Transactions on Electron Devices, 2018, 65, 2863-2869.	3.0	12
22	Suppressed Degradation of Elevated-Metal Metalâ€“Oxide Thin-Film Transistors Under Bipolar Gate Pulse Stress. IEEE Electron Device Letters, 2018, 39, 707-710.	3.9	11
23	Roles of Gate Voltage and Stress Power in Self-Heating Degradation of a-InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 1644-1648.	3.0	10
24	A systematic study of light dependency of persistent photoconductivity in a-InGaZnO thin-film transistors*. Chinese Physics B, 2020, 29, 118101.	1.4	9
25	A Two-Stage Degradation Model of p-Channel Low-Temperature Poly-Si Thin-Film Transistors Under Positive Bias Temperature Stress. IEEE Transactions on Electron Devices, 2011, 58, 3501-3505.	3.0	8
26	Two-Stage Degradation of p-Type Polycrystalline Silicon Thin-Film Transistors Under Dynamic Positive Bias Temperature Stress. IEEE Transactions on Electron Devices, 2014, 61, 3751-3756.	3.0	8
27	Degradation of a-InGaZnO TFTs Under Synchronized Gate and Drain Voltage Pulses. IEEE Transactions on Electron Devices, 2018, 65, 995-1001.	3.0	8
28	TCAD Analysis of the Four-Terminal Poly-Si TFTs on Suppression Mechanisms of the DC and AC Hot-Carrier Degradation. IEEE Journal of the Electron Devices Society, 2019, 7, 606-612.	2.1	8
29	Origin of Degradation of Flexible Poly-Si TFTs Under Dynamic Bending Stress. IEEE Electron Device Letters, 2021, 42, 1627-1630.	3.9	8
30	Hot-Carrier Effects in a-InGaZnO Thin-Film Transistors Under Pulse Drain Bias Stress. IEEE Transactions on Electron Devices, 2021, 68, 2742-2747.	3.0	8
31	Ambient instability of organic field-effect transistors and their improvement strategies. Journal Physics D: Applied Physics, 2022, 55, 053001.	2.8	8
32	Reliability of low-temperature polysilicon thin-film transistors for flexible electronics application. , 2016, , .		7
33	A comparative study of n-channel low temperature poly-Si thin-film transistors with a body terminal or a lightly-doped-drain structure. Semiconductor Science and Technology, 2018, 33, 025003.	2.0	7
34	Investigation of the anomalous hump phenomenon in amorphous InGaZnO thin-film transistors. Solid-State Electronics, 2020, 170, 107814.	1.4	7
35	Finite element analysis of temperature distribution of polycrystalline silicon thin film transistors under self-heating stress. Frontiers of Electrical and Electronic Engineering in China: Selected Publications From Chinese Universities, 2009, 4, 227-233.	0.6	6
36	Origin of Spontaneous Degradation of Flexible Poly-Si TFTs After Dynamic Bending. IEEE Electron Device Letters, 2020, 41, 1205-1208.	3.9	6

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37	A Unified Degradation Model of Elevated-Metal Metal Oxide (EMMO) TFTs Under Positive Gate Bias With or Without an Illumination. IEEE Transactions on Electron Devices, 2021, 68, 1081-1087.	3.0	6
38	Degradation and Failure of Flexible Low-Temperature Poly-Si TFTs Under Dynamic Stretch Stress. IEEE Transactions on Electron Devices, 2021, 68, 4455-4461.	3.0	6
39	Thermal Annealing Improved Stability of Amorphous InGaZnO Thin-Film Transistors Under AC Bias Stresses. IEEE Electron Device Letters, 2021, 42, 1623-1626.	3.9	6
40	Effective Channel Mobility of Poly-Silicon Thin Film Transistors. , 2006, , .		5
41	Comparison of device degradation of n-type metal-induced laterally crystallized poly-Si TFTs with or without hydrogenation. , 2009, , .		5
42	Dynamic HC-induced degradation in n-type poly-Si thin film transistors under off-state gate pulse voltage. , 2013, , .		5
43	Investigations on the Gate-Induced Drain Leakage Current of Polycrystalline-Silicon Thin-Film Transistor and Its Suppression With Drain Bias Sweep. IEEE Transactions on Electron Devices, 2016, 63, 1572-1577.	3.0	5
44	Dynamic degradation mechanisms of low temperature polycrystalline silicon thin-film transistors. , 2012, , .		4
45	Degradation of low temperature poly-Si TFTs under bipolar gate pulses with DC drain bias. , 2016, , .		4
46	Gate Voltage Pulse Rising Edge Dependent Dynamic Hot Carrier Degradation in Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2021, 42, 1615-1618.	3.9	4
47	Bilayer-passivated stable dif-TES-ADT organic thin-film transistors. Applied Physics Letters, 2021, 119, 183301.	3.3	4
48	Characterization of hot carrier degradation in n-type poly-Si TFTs under dynamic drain pulse Stress with DC gate bias. , 2010, , .		3
49	Negative drain pulse stress induced two-stage degradation of P-channel poly-Si thin-film transistors. , 2011, , .		3
50	Investigations on the Negative Shift of the Threshold Voltage of Polycrystalline Silicon Thin-Film Transistors Under Positive Gate Bias Stress. IEEE Transactions on Electron Devices, 2021, 68, 550-555.	3.0	3
51	Statistical Study of Degradation of Flexible Poly-Si TFTs Under Dynamic Bending Stress. IEEE Journal of the Electron Devices Society, 2022, 10, 123-128.	2.1	3
52	Observation of combined self-heating and hot-carrier degradation in n-type poly-Si thin-film transistors. , 2009, , .		1
53	Degradation of Elevated-Metal Metal-Oxide Thin-Film Transistors Under AC Bias Stress. , 2018, , .		1
54	A Physical-Based Analytical Model for the Kink Current of Polycrystalline Silicon TFTs. IEEE Transactions on Electron Devices, 2020, 67, 2359-2364.	3.0	1

#	Article	IF	Citations
55	Reliability of Flexible LTPS TFTs under Dynamic Mechanical Stress. , 2020, , .		1
56	Pâ€2: Reâ€Crystallized Metalâ€Induced Laterally Crystallized Polycrystalline Silicon for Systemâ€onâ€Panel Applications. Digest of Technical Papers SID International Symposium, 2000, 31, 531-533.	0.3	0
57	Degradation and its Fast Recovery in a-IGZO Thin-Film Transistors under Negative Gate Bias Stress. Chinese Physics B, 0, , .	1.4	0
58	Statistical Analysis of Degradation and Failure of Flexible LTPS TFTs under Dynamic Mechanical Stress. , 2021, , .		0